## 257/52, 55,616

	L	Hits	Search Text	DB	Time stamp
11:24	Number	0.10		110 D 2 M	2002/00/22
2   ((qate adj1 electrode) with germanium)   USPAT;   2002/01/23	-	212	(gate ad)1 electrode) with germanium	EPO; JPO;	
					2002/01/02
	-	2			
1			same (conduct\$3 adj1 film)		10:26
and (conduct\$3 adj1 film)  - 9 ((gate adj1 electrode) with germanium) same (stilcon adj1 substrate) same MOSFET  - 2 ((gate adj1 electrode) with germanium) same (stilcon adj1 substrate) same MOSFET  - 31 ((gate adj1 electrode) with germanium) same (stilcon adj1 substrate) same MOSFET  - 31 ((gate adj1 electrode) with germanium) same (stilcon adj1 substrate) and MOSFET  - 31 ((gate adj1 electrode) with germanium) same (stilcon adj1 substrate) and MOSFET  - 31 ((gate adj1 electrode) with germanium) same (stilcon adj1 substrate) and MOSFET  - 32 ((gate adj1 electrode) with germanium) same (stilcon adj1 substrate) and MOSFET  - 31 ((gate adj1 electrode) with germanium) same (spate and silcon adj1 substrate) and MOSFET  - 32 ((gate adj1 electrode) with germanium) same (spate and silcon adj1 substrate) and MOSFET  - 32 ((gate adj1 electrode) with germanium) same (spate and silcon adj1 substrate) same MOSFET  - 10 (conduct\$3 with (transition near3 metal)) same (gate and germanium) same (gate and ge					
	-	13	((gate adjl electrode) with germanium)		
-   9			and (conduct\$3 adj1 film)	EPO; JPO;	10:26
Same (p-type near3 dopS3)			· ·	DERWENT	
Same (p-type near3 dop\$3)	_	9	((gate adil electrode) with germanium)	USPAT:	2002/01/23
Conduct\$3 with (transition near3 metal)   SPRWENT   Same (solicon adja substrate)   Servent				EPO: JPO:	16:26
-			came (p ejpe mana apra)		
	_	2	//gate adil electrode) with germanium)		2002/01/24
SERVENT	_	-			
-			Same (SIIICON adji Subsciace) Same Nosibi		00.55
and (silicon adj1 substrate) and MOSFET   BPO; pot; 10:23		21	(/mate adil electrode) with germanium)		2002/01/24
DERWENT   SUPPAT;   EPO; JPO;   DERWENT   USPAT;   USP	-	31			
11			and (Silicon ad) i substrate) and mostar		10.23
B			#5016031#		2002/01/21
B	1-	11	251.6511		
Second   S	1				13:12
Conduct\$3 with (transition near3 metal)			L		1
DERWENT	-	8	"5101247"		
Conduct\$3 with (transition near3 metal)					13:49
Conduct\$3 with (transition near3 metal)					
Conduct\$3 with (transition near3 metal)   DERWENT   2002/01/31   15:38   2002/01/31   2002/01/	-	2511	conduct\$3 with (transition near3 metal)		
Conduct\$3 with (transition near3 metal)					15:42
and (gate near4 germanium)				DERWENT	
and (gate near's germanium)	l -	0	(conduct\$3 with (transition near3 metal))	USPAT;	2002/01/31
	1			JPO;	15:38
and gate and germanium   JPO;   15:24				DERWENT	
and gate and germanium   JPO;   15:24	_	۹	(conduct\$3 with (transition near3 metal))	USPAT:	2002/01/31
DERMENT   SAME (gate and germanium)   DERMENT   SAME (gate and germanium)   USPAT;   DOZ/02/01/31   DOZ/02/02/01/31   DOZ/02	-	1			
Conduct\$3 with (transition near3 metal)			and gate and germaniam		
Same (gate and germanium)	1_		(conduct93 with (transition near3 metal))		2002/01/31
104   Conduct\$3 with (transition near3 metal)   USPAT; 2002/01/31   Side   Service	1-	١ ،			
104			Same (gace and germanium)		1 20.10
and (metal near2 silicide)  and (metal near2 silicide)  and (metal near2 silicide)  407 (conduct\$3 near3 (film or layer)) with USPAR; 15:59  15:59  DERWENT  USPAR; 2002/01/31  JPO; DERWENT  USPAR; 2002/02/01  10:33  PERWENT  USPAR; 2002/02/01  JPO; DERWENT  USPAR;		104	(		2002/01/31
DERWENT	-	104	(Conducts 3 with (transition hears metal))		
Conduct\$3 near3 (film or layer) with USPAT; 15:59   15:59			and (metal hearz silicide)		15.40
Conduct\$3 near2 (film or layer) and USPAT; 2002/02/01   15:59   15:59   16:33   16:39   16:3					2002/01/21
Segmanium near2 (film or layer) and   Segmanium near2 (film or layer)   Segmanium near2 (layer or film)   Segmanium near2 (layer or film)   Segmanium near2 (film or layer)	-	407			
931   (germanium near2 (film or layer)) and (conduct\$3 near2 (film or layer))   USPAT;   2002/02/01   2002/02/02/01   2002/02/01   2002/02/02/01   2002/02/02/01   2002/02/02/01   2002/02/02/01   2002/02/02/01   2002/02/02/01   2002/02/02/02/02/02/02/02/02/02/02/02/02			(transition near3 metal)		13.39
Conduct\$3 near2 (film or layer)	1				2002/02/01
DERWENT   DERWENT     DERWENT	-	931	(germanium near2 (film or layer)) and		
35609   (polysilicon near2 (layer or film))	1		(conduct\$3 near2 (film or layer))		10:33
150   ([polysilicon near2 (layer or film))   DERWENT   2002/02/01     ([polysilicon near2 (film or layer))   DERWENT   2002/02/01     ([polysilicon layer between a germanium   DERWENT   2002/02/01     ([polysilicon layer between a germanium   DERWENT   10:31   DERWENT   10:33   DERWENT   10:33   DERWENT   10:33   DERWENT   10:33   DERWENT   10:33   DERWENT   10:34   DERWENT   10:36   D	1				2002/02/03
DERWENT	-	35609	(polysilicon near2 (layer or film))		
150   ((polysilicon near2 (layer or film)) and (germanium near2 (ffilm or layer)) and (conduct\$3 near2 (ffilm or layer))   DERWENT   10:31   10:31   10:31   10:31   10:31   10:31   10:31   10:31   10:31   10:31   10:31   10:32   10:33   10:33   10:33   10:33   10:33   10:34					10:27
((germanium near2 (film or layer)) and (conduct\$3 near2 (film or layer))  - 158 (germanium near2 (film or layer)) with (conduct\$3 near2 (film or layer)) USPAT; 2002/02/01 (1:38 DERWENT (conduct\$3 near2 (film or layer)) with (conduct\$3 near2 (film or layer)) with (polyslicon near2 (film or layer)) with (polyslicon near2 (layer or film)) (conduct\$3 near2 (film or layer)) with (conduct\$3 near2 (film or layer)) with (polyslicon near2 (film or layer)) with (conduct\$3 near2 (film or layer)) with (somewhat (conduct\$3 near2 (film or layer)) with (somewhat (germanium near2 (germanium near2)) with (somewhat (germanium near2) (germanium near2)) with (germanium near2) (		1			
	-	150			
-   0		i	((germanium near2 (film or layer)) and		10:31
layer and a conductive layer"	1	1			
layer and a conductive layer"	-	0			
158   (germanium near2 (film or layer)) with   USPAT;   2002/02/01   11:18     11:18     11:18     12:18   12:18     12:18     12:18     12:18     12:18     12:18     12:18     12:18     12:18     12:18     12:18     12:18     12:18   12:18   12:18     1		1			10:33
Conduct\$3 near2 (film or layer)		1			
Conduct\$3 near2 (film or layer)	-	158	(germanium near2 (film or layer)) with	USPAT;	
- 11 ((germanium near2 (film or layer)) with (conduct\$3 near2 (film or layer)) with (polysilicon near2 (layer or film)) - 6 ((germanium near2 (film or layer)) with (conduct\$3 near2 (film or layer)) with (silicide (germanium near2 (film or layer)) with (syaticon near2 (film or layer)) with (syatico	1			JPO;	11:18
(conduct\$3 near2 (film or layer)) with JPO; 10:36  (polysilicon near2 (layer or film)) DERWENT ((germanium near2 (film or layer)) with USPAT; 2002/02/01 (conduct\$3 near2 (film or layer)) with USPAT; 11:00  16:66 (germanium near2 (film or layer)) with USPAT; 2002/02/01 (\$4silicon near2 (film or layer)) with USPAT; 11:23  - 35 ((germanium near2 (film or layer)) with USPAT; 2002/02/01 (\$4silicon near2 (film or layer)) with USPAT; 2002/02/01 (\$4silicon near2 (film or layer)) with USPAT; 11:23	1				
(conduct\$3 near2 (film or layer)) with JPO; 10:36  (polysilicon near2 (layer or film)) DERWENT ((germanium near2 (film or layer)) with USPAT; 2002/02/01 (conduct\$3 near2 (film or layer)) with USPAT; 11:00  16:66 (germanium near2 (film or layer)) with USPAT; 2002/02/01 (\$4silicon near2 (film or layer)) with USPAT; 11:23  - 35 ((germanium near2 (film or layer)) with USPAT; 2002/02/01 (\$4silicon near2 (film or layer)) with USPAT; 2002/02/01 (\$4silicon near2 (film or layer)) with USPAT; 11:23	-	11	((germanium near2 (film or layer)) with	USPAT;	2002/02/01
(polysilicon near2 (layer or film))		1			
- ((germanium near2 (film or layer)) with USPAT; 2002/02/01 (conduct\$3 near2 (film or layer)) with Silicide (germanium near2 (film or layer)) with USPAT; 2002/02/01 (\$4silicon near2 (film or layer)) with USPAT; 2002/02/01 11:23 ((germanium near2 (film or layer)) with USPAT; 2002/02/01 (\$4silicon near2 (film or layer)) with USPAT; 2002					
(conduct\$3 mear2 (film or layer))) with	_	۱ ۵	((germanium near2 (film or laver)) with		2002/02/01
		1	/conduct\$3 near2 (film or layer))) with		
- 1676 (germanium near2 (film or layer)) with USPAT; 2002/02/01 (\$4silicon near2 (film or layer)) JPO; 11:23   11:23   15   15   15   15   15   15   15   1					
(\$4silicon near2 (film or layer)) JPO; 11:23   BERWENT   G(sermanium near2 (film or layer)) with USPAT; 2002/02/01   (\$4silicon near2 (film or layer)) with JPO; 11:23	_	1676			2002/02/01
- 35 ((germanium near2 (film or layer)) with USPAT; 2002/02/01 (\$4sslicon near2 (film or layer))) with JPO; 11:23	-	10/6			
- 35 ((germanium near2 (film or layer)) with USPAT; 2002/02/01 (\$4silicon near2 (film or layer))) with JPO; 11:23	1		(A12TITCOU Heats (TITH OF Taket))		1
(\$4silicon near2 (film or layer))) with JPO; 11:23		3.5	((manmanium mann2 (film on lavami) with		2002/02/01
	1 -	35	((germanium nearz (IIIm or layer)) with		
SILICIDE DERWENT					11.23
	L	1	Silicide	DEKMENT	

Search History 9/9/03 6:01:00 PM Page 1

-	12	"5608249"	USPAT;	2002/02/01
			JPO;	14:09
	83		DERWENT	2002/09/15
-	83	(gate adj (dielectric or insulator)) with (germanium or ge)	USPAT; EPO; JPO;	19:03
		(germanium or ge)	DERWENT	19.03
1.	67	((gate adj (dielectric or insulator))	USPAT;	2002/09/15
-	07	with (germanium or ge)) and @ad<19992306	EPO; JPO;	19:05
	1	with (germanium of ge), and eactrosses	DERWENT	13.00
_	58	((gate ad) (dielectric or insulator))	USPAT;	2002/09/22
		with (germanium or ge)) and @ad<19990623	EPO; JPO;	09:08
		, , , , , , , , , , , , , , , , , , ,	DERWENT	
-	18	((germanium or ge) adj (film or layer))	USPAT;	2002/09/19
		with (gate adj insulat\$3)	EPO; JPO;	15:59
			DERWENT	
-	16	(((germanium or ge) adj (film or layer))	USPAT;	2002/09/19
	1	with (gate adj insulat\$3)) and	EPO; JPO;	16:00
		@ad<19990623	DERWENT	
-	19	(((gate adj electrode) with (germanium or	USPAT;	2002/09/22
		ge)) and @ad<19990623) and ((gate adj	EPO; JPO;	09:11
	1	(insulator or dielectric)) with (germanium or ge))	DERWENT	
1_	382	(germanium or ge) ((gate adj electrode) with (germanium or	USPAT;	2002/09/22
1	302	qe)) and @ad<19990623	EPO; JPO;	09:27
		ge// and ead(19990025	DERWENT	05.27
_	157	((gate adjl electrode) with (germanium or	USPAT;	2003/04/11
	157	ge)) same (gate adj (dielectric or	US-PGPUB;	14:01
		insulat\$3 or \$20xide)) and (dop\$3 same	EPO; JPO;	
	I	("p-type" or boron or b or al or aluminum	DERWENT	
		or ga or in))		
-	44	(((gate adj1 electrode) with (germanium	USPAT;	2003/04/11
	1	or ge)) same (gate adj (dielectric or	US-PGPUB;	15:30
		insulat\$3 or \$2oxide)) and (dop\$3 same	EPO; JPO;	
		("p-type" or boron or b or al or aluminum	DERWENT	
1		or ga or in))) and @ad<19990623		
-	0	(germanium near3 gate) same	USPAT;	2003/04/11
		"1.times.10.sup.\$2"	US-PGPUB;	15:21
	i		EPO; JPO; DERWENT	
	3	(germanium near3 gate) same	USPAT:	2003/04/11
-	,	("1.times.10.sup.17" or	US-PGPUB;	15:25
		"1.times.10.sup.18" or	EPO; JPO;	10,20
		"1.times.10.sup.19" or	DERWENT	
1	1	"1.times.10.sup.20")		
-	3	(germanium with gate with electrode) same	USPAT;	2003/04/11
1		("1.times.10.sup.17" or	US-PGPUB;	16:00
1		"1.times.10.sup.18" or	EPO; JPO;	
		"1.times.10.sup.19" or	DERWENT	
		"1.times.10.sup.20")	HCDAT.	2003/04/11
1-	20	(germanium with film) same "p-type" same impurities same dop\$3	USPAT; US-PGPUB;	15:29
		Impurites same dob22	EPO; JPO;	10.45
			DERWENT	
1 -	15	((germanium with film) same "p-type" same	USPAT;	2003/04/11
1	1	impurities same dop\$3) and @ad<19990623	US-PGPUB;	16:00
			EPO; JPO;	
			DERWENT	
-	44	(germanium with film) same	USPAT;	2003/04/11
		("1.times.10.sup.17" or	US-PGPUB;	16:13
		"1.times.10.sup.18" or	EPO; JPO;	
		"1.times.10.sup.19" or	DERWENT	
		"1.times.10.sup.20")		l
-	19	((germanium with film) same	USPAT;	2003/04/11
		("1.times.10.sup.17" or	US-PGPUB;	16:12
		"1.times.10.sup.18" or	EPO; JPO;	1
		"1.times.10.sup.19" or	DERWENT	
1_	701	"1.times.10.sup.20")) and @ad<19990623 (ge or germanium) with "above" with oxide	USPAT;	2003/04/11
1-	/01	(ge or germanium) with above with oxide	US-PGPUB;	16:12
	1		EPO; JPO;	
			DERWENT	
		L	1	

-	519	((ge or germanium) with "above" with oxide) and @ad<19990623	USPAT; US-PGPUB;	2003/04/11 17:00
			EPO; JPO;	/
	7	(((ge or germanium) with "above" with	DERWENT USPAT;	2003/04/11
-	· '	oxide) and @ad<19990623) and	US-PGPUB;	17:08
		("1.times.10.sup.17" or	EPO; JPO;	17.00
		"1.times.10.sup.18" or	DERWENT	
		"1.times.10.sup.19" or		
		"1.times.10.sup.20")		
-	13	(((ge or germanium) with "above" with	USPAT;	2003/04/11
		oxide) and @ad<19990623) and (gate adj	US-PGPUB;	16:58
		(dielectric or oxide or insulat\$3)) and	EPO; JPO;	
		(gate adj electrode) and "p-type"	DERWENT USPAT;	2003/04/11
_		(germanium adj gate adj electrode) with "on" with (insulat\$3 or oxide)	US-PGPUB;	17:00
		on with (insulate)	EPO; JPO;	17.00
			DERWENT	
-	27	germanium adj gate adj electrode	USPAT;	2003/04/11
	Į.		US-PGPUB;	17:00
1			EPO; JPO;	
	ļ		DERWENT	
-	3	(germanium adj gate adj electrode) and	USPAT;	2003/04/11
		@ad<19990623	US-PGPUB;	17:17
	1		EPO; JPO; DERWENT	
_	45	((ge or germanium) with electrode) same	USPAT;	2003/04/11
-	13	("p-type" or boron) same	US-PGPUB;	17:18
		("1.times.10.sup.17" or	EPO; JPO;	
		"1.times.10.sup.18" or	DERWENT	
		"1.times.10.sup.19" or		
		"1.times.10.sup.20")		
-	33	(((ge or germanium) with electrode) same	USPAT;	2003/04/11
1		("p-type" or boron) same ("1.times.10.sup.17" or	US-PGPUB; EPO; JPO;	17:40
ì		"1.times.10.sup.18" or	DERWENT	
		"1.times.10.sup.19" or	DEIMBIL	
		"1.times.10.sup.20")) and @ad<19990623		
-	3	((ge or germanium) with electrode with	USPAT;	2003/08/13
	l	gate) same ("p-type" or boron) same	US-PGPUB;	17:31
		("1.times.10.sup.17" or	EPO; JPO;	
		"1.times.10.sup.18" or	DERWENT	
		"1.times.10.sup.19" or		
_	5	((ge or germanium) with gate) same	USPAT;	2003/04/11
		("p-type" or boron) same	US-PGPUB;	17:34
		("1.times.10.sup.17" or	EPO; JPO;	
	1	"1.times.10.sup.18" or	DERWENT	
1	1	"1.times.10.sup.19" or	1	
	_	"1.times.10.sup.20") (germanium same (metal adj silicide) same	USPAT;	2003/04/11
-		polysilicon same (metal adj silicide) same   polysilicon same (gate adj electrode))	US-PGPUB;	17:42
	1	and Gad<19990623	EPO; JPO;	212
	1		DERWENT	
-	36	(germanium same (metal adj silicide) same	USPAT;	2003/04/11
	1	polysilicon) and @ad<19990623	US-PGPUB;	18:03
	[		EPO; JPO;	
		(	DERWENT	2002/04/11
~	50	(germanium with (work adj function)) same	USPAT; US-PGPUB;	2003/04/11
	1	(silicon with (work adj function))	EPO; JPO;	10.13
	1		DERWENT	
-	17	germanium with (work adj function) with	USPAT;	2003/04/11
	1	"ev"	US-PGPUB;	18:14
			EPO; JPO;	
	1		DERWENT	1
-	283	((gate adj1 electrode) with (germanium or	USPAT;	2003/08/13
		ge)) same ("p-type" or b or boron or aluminum or indium or gallium)	US-PGPUB; EPO; JPO;	17:49
		aruminum of indium of garrium)	DERWENT	

-	41	(((gate adj1 electrode) with (germanium	USPAT;	2003/08/13
		or ge)) same ("p-type" or b or boron or	US-PGPUB;	17:50
		aluminum or indium or gallium)) and	EPO; JPO;	
		("1.times.10.sup.17" or	DERWENT	
		"1.times.10.sup.18" or		
		"1.times.10.sup.19" or		
		"1.times.10.sup.20")		
-	20		USPAT;	2003/08/13
		or ge)) same ("p-type" or b or boron or	US-PGPUB;	18:21
		aluminum or indium or gallium)) and	EPO; JPO;	
		("1.times.10.sup.17" or	DERWENT	
		"1.times.10.sup.18" or		
		"1.times.10.sup.19" or		
		"1.times.10.sup.20")) and @ad<19990623		
-	814	(gate adil electrode) with (germanium or	USPAT;	2003/08/13
		ge)	US-PGPUB;	17:49
		1 7	EPO; JPO;	l .
			DERWENT	
-	8	((gate ad]1 electrode) with (germanium or	USPAT;	2003/08/13
		ge)) same ("1.times.10.sup.17" or	US-PGPUB;	17:55
		"1.times.10.sup.18" or	EPO; JPO;	
		"1.times.10.sup.19" or	DERWENT	
		"1.times.10.sup.20")		1
-	2	("5952701"   "6262456"	USPAT	2003/08/13
	_	"2002/0113294").PN.		17:52
-	2	(work adj function) same (germanium or	USPAT;	2003/08/13
	_	ge) same (mid with gap with energy with	US-PGPUB;	18:19
		silicon)	EPO; JPO;	
		·	DERWENT	
-	0	1111686.URPN.	USPAT	2003/08/13
				18:05
-	5		USPAT	2003/08/13
		"5250818"   "5619057").PN.		18:05
-	39	(boron or b) with implant\$5 with	USPAT;	2003/08/13
		(germanium or ge) with "kev"	US-PGPUB;	18:20
		**	EPO; JPO;	
			DERWENT	
-	20		USPAT;	2003/08/13
	1	(germanium or ge) with "kev") and	US-PGPUB;	18:21
		@ad<19990623	EPO; JPO;	
1			DERWENT	
-	31		USPAT;	2003/08/13
	1	ge) with (gate adj electrode) with	US-PGPUB;	18:46
		(boron or b)	EPO; JPO;	l .
			DERWENT	
-	13	((dop\$3 or implant\$5) with (germanium or	USPAT;	2003/08/13
	l	ge) with (gate ad) electrode) with	US-PGPUB;	18:46
	1	(boron or b)) and @ad<19990623	EPO; JPO;	
	1		DERWENT	
-	0	jp-27854-\$.did	USPAT;	2003/08/22
	1		EPO; JPO;	11:24
			DERWENT	
-	0	jp-1027854-\$.did	USPAT;	2003/08/22
			EPO; JPO;	11:24
1	l		DERWENT	